

# BZV55 series

## Voltage regulator diodes

Rev. 04 — 19 July 2007

勝特力材料 886-3-5753170  
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Product data sheet

## 1. Product profile

### 1.1 General description

Low-power voltage regulator diodes in small hermetically sealed glass SOD80C Surface-Mounted Device (SMD) packages. The diodes are available in the normalized E24  $\pm 2\%$  (BZV55-B) and approximately  $\pm 5\%$  (BZV55-C) tolerance range. The series consists of 37 types with nominal working voltages from 2.4 V to 75 V.

### 1.2 Features

- Non-repetitive peak reverse power dissipation:  $\leq 40$  W
- Total power dissipation:  $\leq 500$  mW
- Two tolerance series:  $\pm 2\%$  and  $\pm 5\%$
- Wide working voltage range: nominal 2.4 V to 75 V (E24 range)
- Low differential resistance
- Small hermetically sealed glass SMD package

### 1.3 Applications

- General regulation functions

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_F$	forward voltage	$I_F = 10$ mA	-	-	0.9	V
$P_{ZSM}$	non-repetitive peak reverse power dissipation	[1]	-	-	40	W

[1]  $t_p = 100$   $\mu$ s; square wave;  $T_j = 25$  °C prior to surge

## 2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Symbol
1	cathode	[1]	
2	anode		

[1] The marking band indicates the cathode.

### 3. Ordering information

Table 3. Ordering information

Type number	Package		Version
	Name	Description	
BZV55-B2V4 to BZV55-C75 <sup>[1]</sup>	-	hermetically sealed glass surface-mounted package; 2 connectors	SOD80C

[1] The series consists of 74 types with nominal working voltages from 2.4 V to 75 V.

### 4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
BZV55-B2V4 to BZV55-C75	marking band

[1] blue: made in China  
 yellow: made in Philippines

### 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$I_F$	forward current		-	250	mA
$I_{ZSM}$	non-repetitive peak reverse current		<sup>[1]</sup> -	see Table 8 and 9	
$P_{ZSM}$	non-repetitive peak reverse power dissipation		<sup>[1]</sup> -	40	W
$P_{tot}$	total power dissipation	$T_{amb} \leq 50\text{ °C}$	<sup>[2]</sup> -	400	mW
		$T_{tp} \leq 50\text{ °C}$	<sup>[2]</sup> -	500	mW
$T_{stg}$	storage temperature		-65	+200	°C
$T_j$	junction temperature		-65	+200	°C

[1]  $t_p = 100\ \mu\text{s}$ ; square wave;  $T_j = 25\text{ °C}$  prior to surge

[2] Device mounted on a ceramic substrate of  $10 \times 10 \times 0.6\text{ mm}$ .

### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<sup>[1]</sup> -	-	380	K/W
$R_{th(j-t)}$	thermal resistance from junction to tie-point		-	-	300	K/W

[1] Device mounted on a ceramic substrate of  $10 \times 10 \times 0.6\text{ mm}$ .

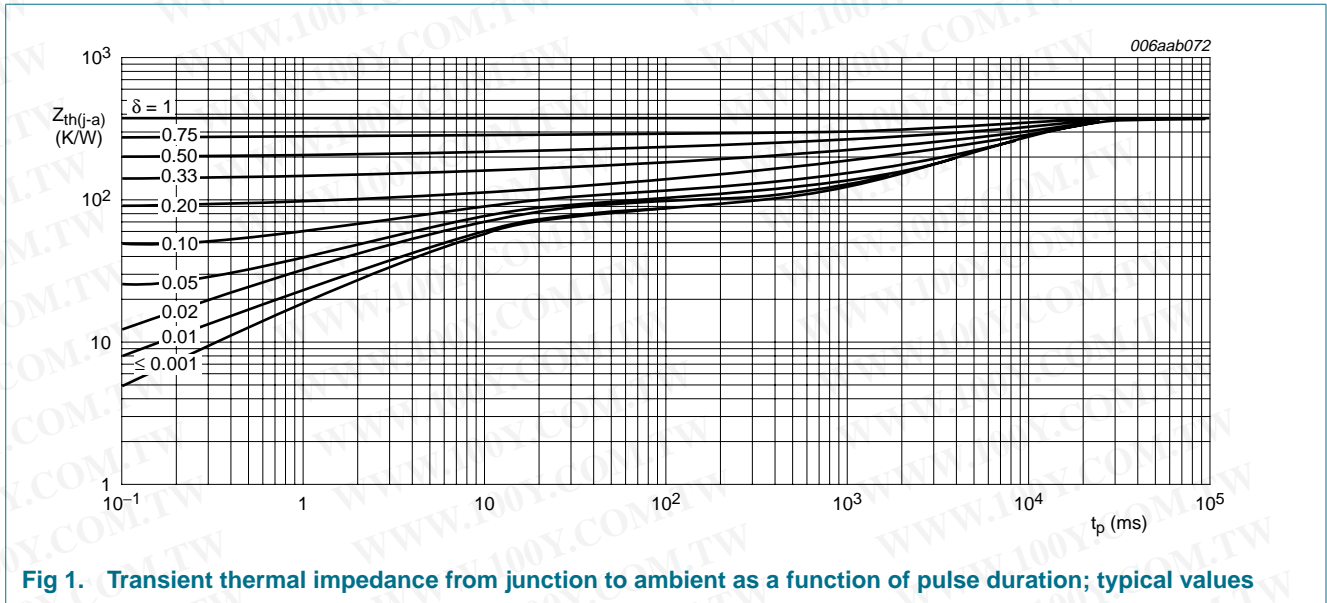


Fig 1. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 7. Characteristics

**Table 7. Characteristics**  
 $T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_F$	forward voltage	$I_F = 10\text{ mA}$	-	-	0.9	V
$I_R$	reverse current					
	BZV55-B/C2V4	$V_R = 1\text{ V}$	-	-	50	$\mu\text{A}$
	BZV55-B/C2V7	$V_R = 1\text{ V}$	-	-	20	$\mu\text{A}$
	BZV55-B/C3V0	$V_R = 1\text{ V}$	-	-	10	$\mu\text{A}$
	BZV55-B/C3V3	$V_R = 1\text{ V}$	-	-	5	$\mu\text{A}$
	BZV55-B/C3V6	$V_R = 1\text{ V}$	-	-	5	$\mu\text{A}$
	BZV55-B/C3V9	$V_R = 1\text{ V}$	-	-	3	$\mu\text{A}$
	BZV55-B/C4V3	$V_R = 1\text{ V}$	-	-	3	$\mu\text{A}$
	BZV55-B/C4V7	$V_R = 2\text{ V}$	-	-	3	$\mu\text{A}$
	BZV55-B/C5V1	$V_R = 2\text{ V}$	-	-	2	$\mu\text{A}$
	BZV55-B/C5V6	$V_R = 2\text{ V}$	-	-	1	$\mu\text{A}$
	BZV55-B/C6V2	$V_R = 4\text{ V}$	-	-	3	$\mu\text{A}$
	BZV55-B/C6V8	$V_R = 4\text{ V}$	-	-	2	$\mu\text{A}$
	BZV55-B/C7V5	$V_R = 5\text{ V}$	-	-	1	$\mu\text{A}$
	BZV55-B/C8V2	$V_R = 5\text{ V}$	-	-	700	nA
	BZV55-B/C9V1	$V_R = 6\text{ V}$	-	-	500	nA
	BZV55-B/C10	$V_R = 7\text{ V}$	-	-	200	nA
	BZV55-B/C11	$V_R = 8\text{ V}$	-	-	100	nA
	BZV55-B/C12	$V_R = 8\text{ V}$	-	-	100	nA
	BZV55-B/C13	$V_R = 8\text{ V}$	-	-	100	nA
	BZV55-B/C15 to BZV55-B/C75	$V_R = 0.7V_{Z(\text{nom})}$	-	-	50	nA

**Table 8. Characteristics per type; BZV55-B2V4 to BZV55-C24**

$T_j = 25^\circ\text{C}$  unless otherwise specified.

BZV55-xx	Sel	Working voltage $V_Z$ (V)		Differential resistance $r_{\text{dif}}$ ( $\Omega$ )				Temperature coefficient $S_Z$ (mV/K)			Diode capacitance $C_d$ (pF) <sup>[1]</sup>	Non-repetitive peak reverse current $I_{ZSM}$ (A) <sup>[2]</sup>
				$I_Z = 1\text{ mA}$		$I_Z = 5\text{ mA}$		$I_Z = 5\text{ mA}$				
		Min	Max	Typ	Max	Typ	Max	Min	Typ	Max	Max	Max
2V4	B	2.35	2.45	275	600	70	100	-3.5	-1.6	0	450	6.0
	C	2.2	2.6									
2V7	B	2.65	2.75	300	600	75	100	-3.5	-2.0	0	450	6.0
	C	2.5	2.9									
3V0	B	2.94	3.06	325	600	80	95	-3.5	-2.1	0	450	6.0
	C	2.8	3.2									
3V3	B	3.23	3.37	350	600	85	95	-3.5	-2.4	0	450	6.0
	C	3.1	3.5									
3V6	B	3.53	3.67	375	600	85	90	-3.5	-2.4	0	450	6.0
	C	3.4	3.8									
3V9	B	3.82	3.98	400	600	85	90	-3.5	-2.5	0	450	6.0
	C	3.7	4.1									
4V3	B	4.21	4.39	410	600	80	90	-3.5	-2.5	0	450	6.0
	C	4.0	4.6									
4V7	B	4.61	4.79	425	500	50	80	-3.5	-1.4	0.2	300	6.0
	C	4.4	5.0									
5V1	B	5.0	5.2	400	480	40	60	-2.7	-0.8	1.2	300	6.0
	C	4.8	5.4									
5V6	B	5.49	5.71	80	400	15	40	-2.0	1.2	2.5	300	6.0
	C	5.2	6.0									
6V2	B	6.08	6.32	40	150	6	10	0.4	2.3	3.7	200	6.0
	C	5.8	6.6									
6V8	B	6.66	6.94	30	80	6	15	1.2	3.0	4.5	200	6.0
	C	6.4	7.2									
7V5	B	7.35	7.65	30	80	6	15	2.5	4.0	5.3	150	4.0
	C	7.0	7.9									
8V2	B	8.04	8.36	40	80	6	15	3.2	4.6	6.2	150	4.0
	C	7.7	8.7									
9V1	B	8.92	9.28	40	100	6	15	3.8	5.5	7.0	150	3.0
	C	8.5	9.6									
10	B	9.8	10.2	50	150	8	20	4.5	6.4	8.0	90	3.0
	C	9.4	10.6									
11	B	10.8	11.2	50	150	10	20	5.4	7.4	9.0	85	2.5
	C	10.4	11.6									
12	B	11.8	12.2	50	150	10	25	6.0	8.4	10.0	85	2.5
	C	11.4	12.7									

**Table 8. Characteristics per type; BZV55-B2V4 to BZV55-C24 ...continued**

$T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified.

BZV55-x xx	Sel	Working voltage $V_Z$ (V)		Differential resistance $r_{\text{dif}}$ ( $\Omega$ )				Temperature coefficient $S_Z$ (mV/K)			Diode capacitance $C_d$ (pF) <sup>[1]</sup>	Non-repetitive peak reverse current $I_{ZSM}$ (A) <sup>[2]</sup>
				$I_Z = 1\text{ mA}$		$I_Z = 5\text{ mA}$		$I_Z = 5\text{ mA}$				
		Min	Max	Typ	Max	Typ	Max	Min	Typ	Max	Max	Max
13	B	12.7	13.3	50	170	10	30	7.0	9.4	11.0	80	2.5
	C	12.4	14.1									
15	B	14.7	15.3	50	200	10	30	9.2	11.4	13.0	75	2.0
	C	13.8	15.6									
16	B	15.7	16.3	50	200	10	40	10.4	12.4	14.0	75	1.5
	C	15.3	17.1									
18	B	17.6	18.4	50	225	10	45	12.4	14.4	16.0	70	1.5
	C	16.8	19.1									
20	B	19.6	20.4	60	225	15	55	12.3	15.6	18.0	60	1.5
	C	18.8	21.2									
22	B	21.6	22.4	60	250	20	55	14.1	17.6	20.0	60	1.25
	C	20.8	23.3									
24	B	23.5	24.5	60	250	25	70	15.9	19.6	22.0	55	1.25
	C	22.8	25.6									

[1]  $f = 1\text{ MHz}$ ;  $V_R = 0\text{ V}$

[2]  $t_p = 100\text{ }\mu\text{s}$ ; square wave;  $T_j = 25\text{ }^\circ\text{C}$  prior to surge

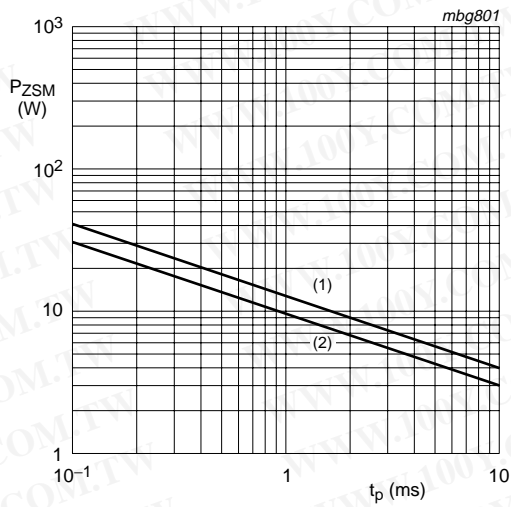
**Table 9. Characteristics per type; BZV55-B27 to BZV55-C75**

$T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified.

BZV55-x xx	Sel	Working voltage $V_Z$ (V)		Differential resistance $r_{\text{dif}}$ ( $\Omega$ )				Temperature coefficient $S_Z$ (mV/K)			Diode capacitance $C_d$ (pF) <sup>[1]</sup>	Non-repetitive peak reverse current $I_{ZSM}$ (A) <sup>[2]</sup>
				$I_Z = 0.5\text{ mA}$		$I_Z = 2\text{ mA}$		$I_Z = 2\text{ mA}$				
		Min	Max	Typ	Max	Typ	Max	Min	Typ	Max	Max	Max
27	B	26.5	27.5	65	300	25	80	18.0	22.7	25.3	50	1.0
	C	25.1	28.9									
30	B	29.4	30.6	70	300	30	80	20.6	25.7	29.4	50	1.0
	C	28.0	32.0									
33	B	32.3	33.7	75	325	35	80	23.3	28.7	33.4	45	0.9
	C	31.0	35.0									
36	B	35.3	36.7	80	350	35	90	26.0	31.8	37.4	45	0.8
	C	34.0	38.0									
39	B	38.2	39.8	80	350	40	130	28.7	34.8	41.2	45	0.7
	C	37.0	41.0									
43	B	42.1	43.9	85	375	45	150	31.4	38.8	46.6	40	0.6
	C	40.0	46.0									
47	B	46.1	47.9	85	375	50	170	35.0	42.9	51.8	40	0.5
	C	44.0	50.0									
51	B	50.0	52.0	90	400	60	180	38.6	46.9	57.2	40	0.4
	C	48.0	54.0									
56	B	54.9	57.1	100	425	70	200	42.2	52.0	63.8	40	0.3
	C	52.0	60.0									
62	B	60.8	63.2	120	450	80	215	58.8	64.4	71.6	35	0.3
	C	58.0	66.0									
68	B	66.6	69.4	150	475	90	240	65.6	71.7	79.8	35	0.25
	C	64.0	72.0									
75	B	73.5	76.5	170	500	95	255	73.4	80.2	88.6	35	0.2
	C	70.0	79.0									

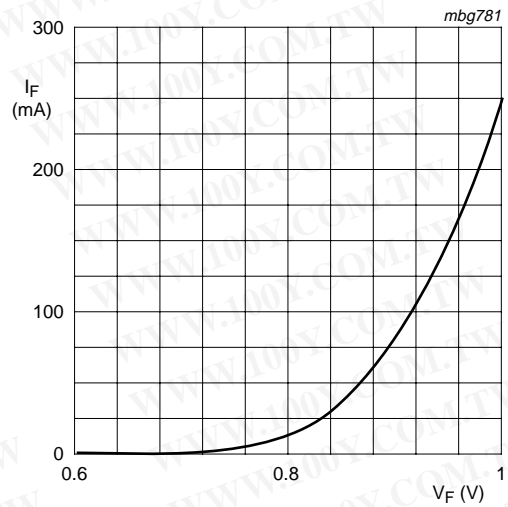
[1]  $f = 1\text{ MHz}$ ;  $V_R = 0\text{ V}$

[2]  $t_p = 100\text{ }\mu\text{s}$ ; square wave;  $T_j = 25\text{ }^\circ\text{C}$  prior to surge



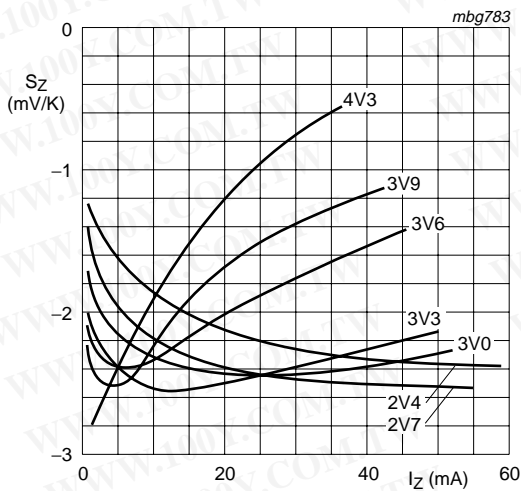
- (1) T<sub>j</sub> = 25 °C (prior to surge)
- (2) T<sub>j</sub> = 150 °C (prior to surge)

**Fig 2. Non-repetitive peak reverse power dissipation as a function of pulse duration; maximum values**



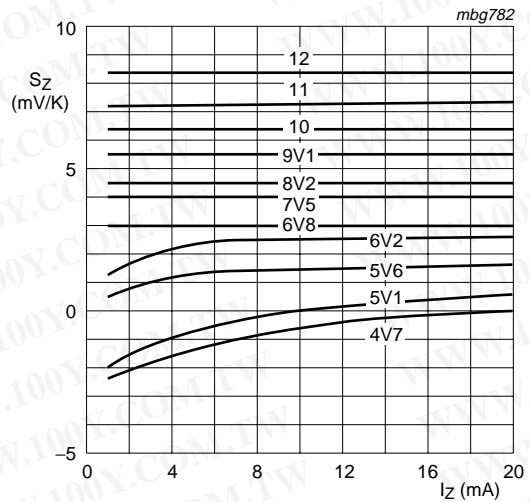
T<sub>j</sub> = 25 °C

**Fig 3. Forward current as a function of forward voltage; typical values**



BZV55-B/C2V4 to BZV55-B/C4V3  
 T<sub>j</sub> = 25 °C to 150 °C

**Fig 4. Temperature coefficient as a function of working current; typical values**



BZV55-B/C4V7 to BZV55-B/C12  
 T<sub>j</sub> = 25 °C to 150 °C

**Fig 5. Temperature coefficient as a function of working current; typical values**

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**8. Package outline**

Hermetically sealed glass surface-mounted package; 2 connectors

SOD80C

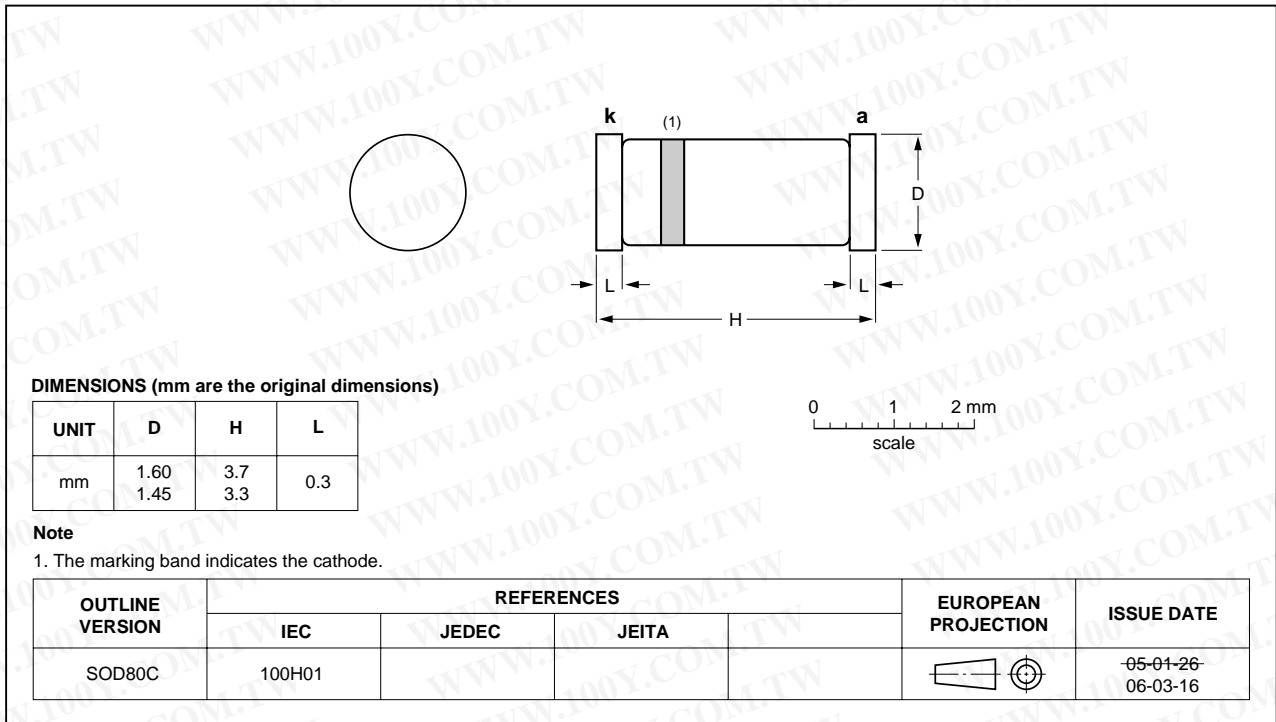


Fig 6. Package outline SOD80C

**9. Packing information**

**Table 10. Packing methods**

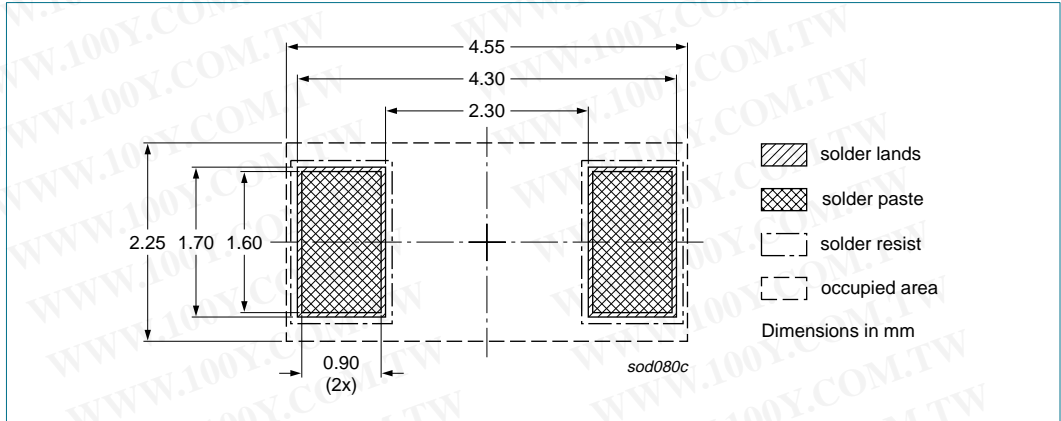
The indicated -xxx are the last three digits of the 12NC ordering code.<sup>[1]</sup>

Type number	Package	Description	Packing quantity	
			2500	10000
BZV55-B2V4 to BZV55-C75	SOD80C	4 mm pitch, 8 mm tape and reel	-115	-135

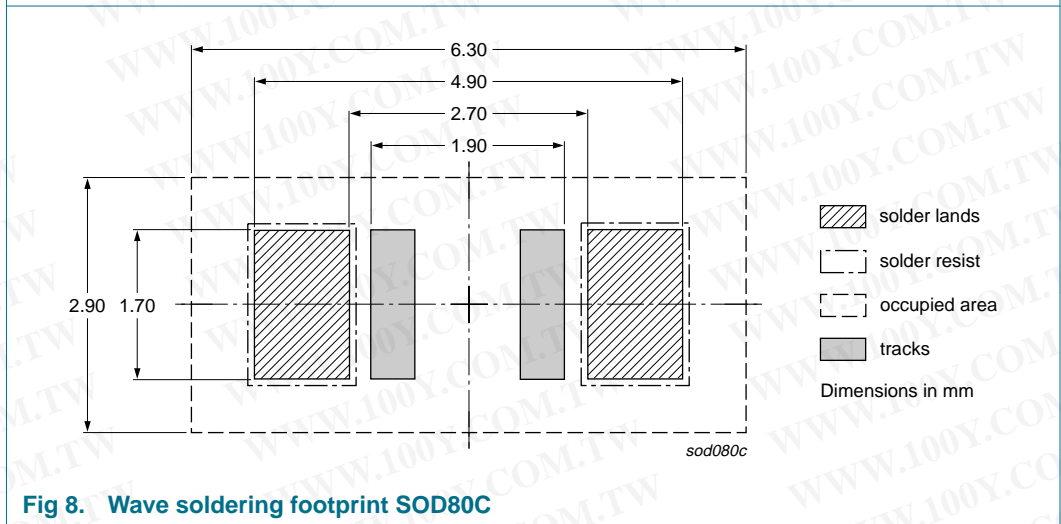
[1] For further information and the availability of packing methods, see [Section 13](#).

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**10. Soldering**



**Fig 7. Reflow soldering footprint SOD80C**



**Fig 8. Wave soldering footprint SOD80C**

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## 11. Revision history

**Table 11. Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
BZV55_SER_4	20070719	Product data sheet	CPCN200508022F	BZV55_3
Modifications:	<ul style="list-style-type: none"> <li>• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li> <li>• Legal texts have been adapted to the new company name where appropriate.</li> <li>• <a href="#">Section 4 “Marking”</a>: enhanced as per CPCN200508022F</li> <li>• <a href="#">Table 5</a>: I<sub>F</sub> continuous forward current redefined to forward current</li> <li>• <a href="#">Table 6</a>: R<sub>th(j-tp)</sub> thermal resistance from junction to tie-point redefined to R<sub>th(j-t)</sub></li> <li>• <a href="#">Figure 1</a>: amended</li> <li>• <a href="#">Section 9 “Packing information”</a>: added</li> <li>• <a href="#">Section 12 “Legal information”</a>: updated</li> </ul>			
BZV55_3	20020228	Product specification	-	BZV55_2
BZV55_2	19990521	Product specification	-	BZV55_1
BZV55_1	19960426	Product specification	-	-

## 12. Legal information

### 12.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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